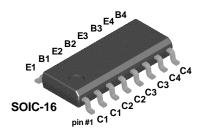


MMPQ2907



PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MMPQ2907	
P _D	Total Device Dissipation Derate above 25°C	1,000 8.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	125 240	°C/W °C/W °C/W

^{*}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

^{**}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

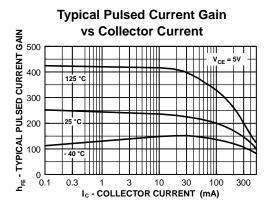
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CLIAF					
OFF CHAR	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _{EBO}	Emitter Cutoff Current	V _{EB} = 30 V		50	nA
I _{CBO}	Collector Cutoff Current	V _{CB} = 30 V		50	nA

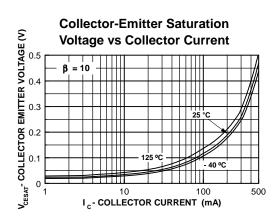
ON CHARACTERISTICS

h _{FE}	DC Current Gain	I _C = 10 mA, V _{CE} = 10 V	75		
		$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}^*$	100	300	
		$I_C = 300 \text{ mA}, V_{CE} = 10 \text{ V}$	30		
		$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}^*$	50		
V _{CE(sat)}	Collector-Emitter Saturation	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$		0.4	V
	Voltage*	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		1.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}^*$		1.3	V
		$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		2.6	V

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

Typical Characteristics





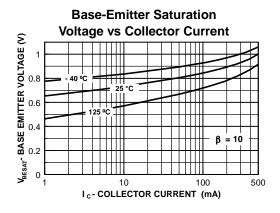
Spice Model

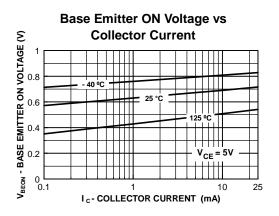
 $PNP \ (Is=650.6E-18 \ Xti=3 \ Eg=1.11 \ Vaf=115.7 \ Bf=231.7 \ Ne=1.829 \ Is=54.81f \ Ikf=1.079 \ Xtb=1.5 \ Br=3.563 \ Nc=2 \ Isc=0 \ Ikr=0 \ Rc=.715 \ Cjc=14.76p \ Mjc=.5383 \ Vjc=.75 \ Fc=.5 \ Cje=19.82p \ Mje=.3357 \ Vje=.75 \ Tr=111.3n \ Tf=603.7p \ Itf=.65 \ Vtf=5 \ Xtf=1.7 \ Rb=10)$

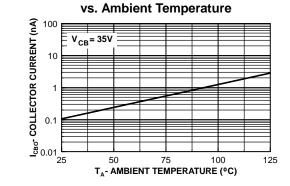
PNP General Purpose Amplifier

(continued)

Typical Characteristics (continued)



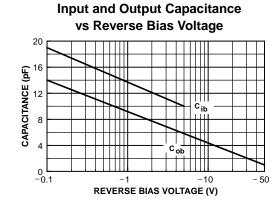


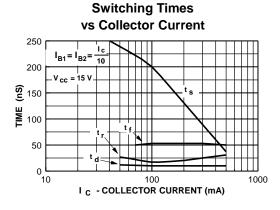


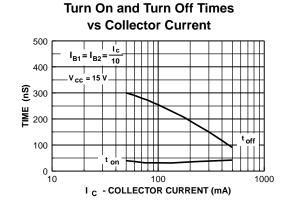
T_A- AMBIENT TEMPERATURE (°C)

125

Collector-Cutoff Current



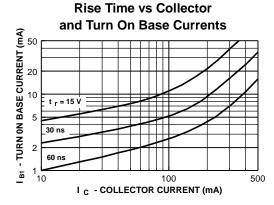


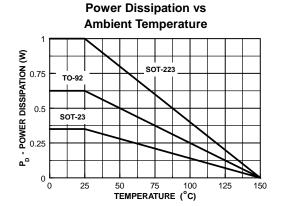


PNP General Purpose Amplifier

(continued)

Typical Characteristics (continued)





Test Circuits

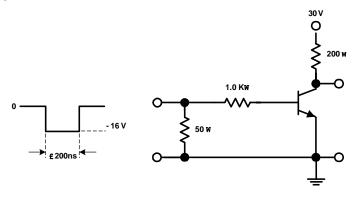


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

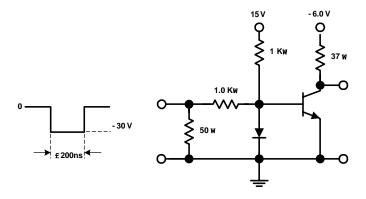


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit

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CROSSVOLT™	GTO™	QFET™	SyncFET™
DenseTrench™	HiSeC™	QS™	TinyLogic™
DOME™	ISOPLANAR™	QT Optoelectronics™	UHC™
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